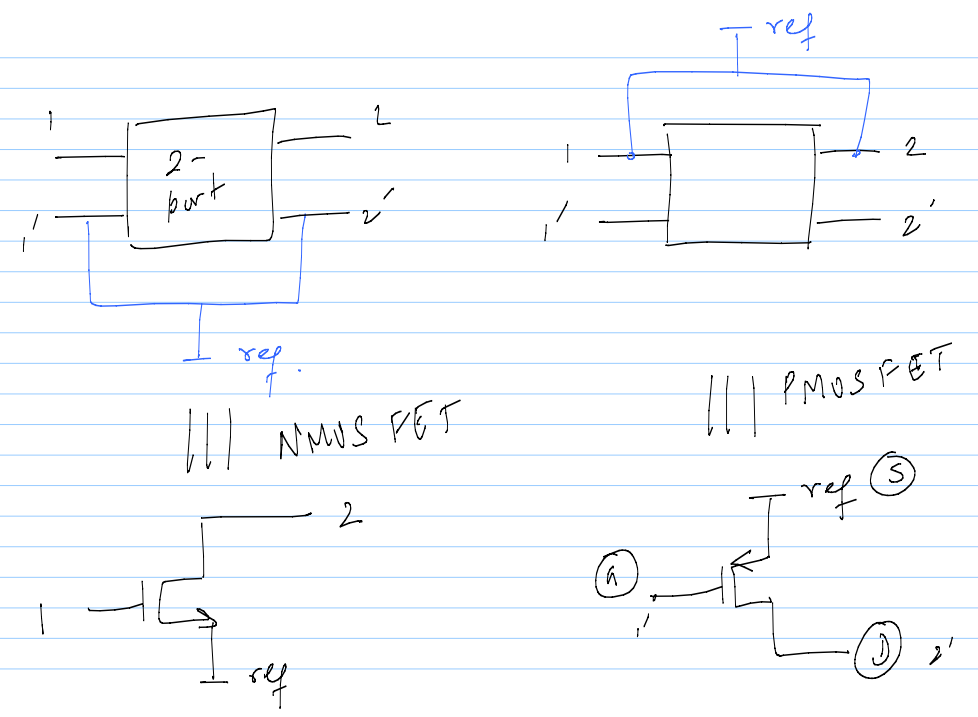
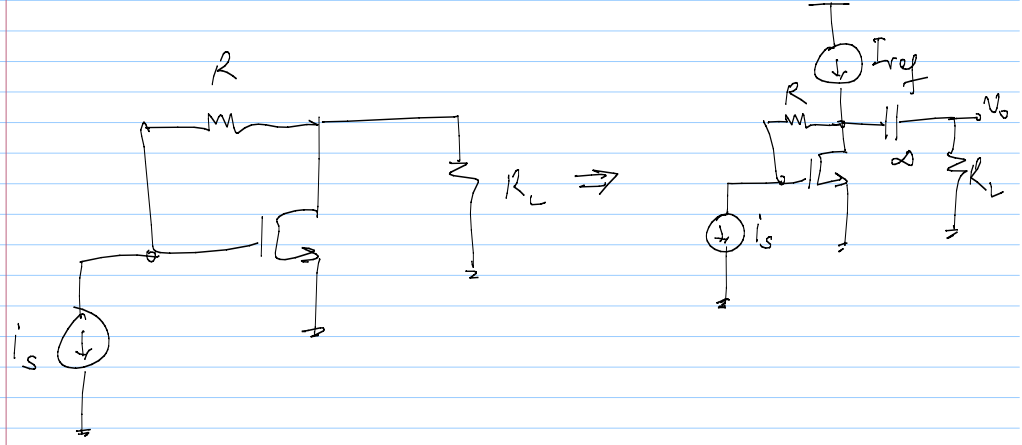


29/9/14

lec 28



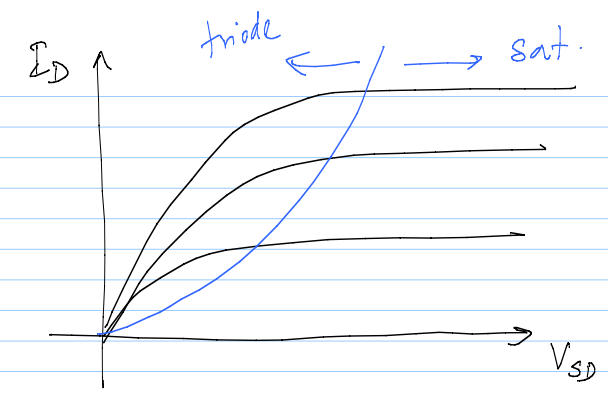
$\downarrow I_D$ $\downarrow I_{D_{NMOS}}$	$\downarrow I_D$ $\downarrow I_{D_{PMOS}}$
* I_D flows into (D)	I_D flows out of (D)
* For sat., $V_D \gg V_S$	For sat.: $V_D \ll V_S$
$V_D \gg V_{th} - V_T$	$V_D \leq V_{th} + V_T$
* $V_{th} \geq V_{Tn}$ for $I_D > 0$	$V_{sa} \geq V_{Tp}$ for $I_D > 0$
* $V_{Tn} > 0$ for enhancement device	$V_{Tp} > 0$ for an enh. device

Sat

$$I_D = \frac{1}{2} M_p \mu_n \left(\frac{W}{L}\right) [V_{sa} - V_{Tp}]^2 \left[1 + \lambda \frac{V_{SD}}{V_{DD}}\right]$$

non-sat.:

$$I_D = M_p \mu_n \left(\frac{W}{L}\right) \left[(V_{sa} - V_{Tp}) V_{SD} - \frac{V_{SD}^2}{2} \right]$$



PMOS
output
char.

Small-signal

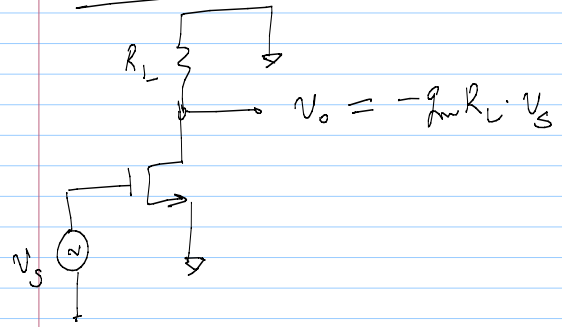
$$y_{11} = 0, \quad y_{12} = 0$$

$$y_{21} = g_m = M_p \mu_n \left(\frac{W}{L}\right) [V_{sa} - V_{Tp}]$$

$$y_{22} = \frac{1}{r_{ds}} = g_{ds} = \lambda_p I_D$$

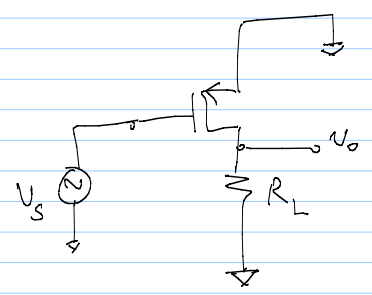
Common-Source Amp:

NMOS

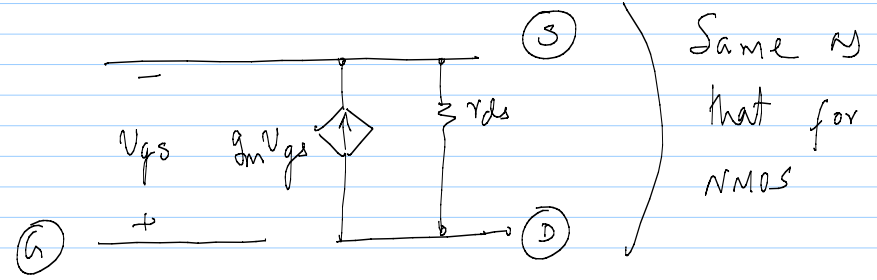
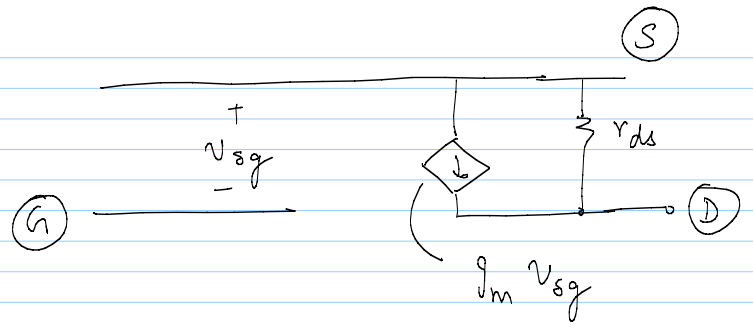


$$\frac{V_o}{V_s} = -g_m R_L$$

PMOS



$$\frac{V_o}{V_s} = -g_m R_L$$



Same μ that for NMOS

